

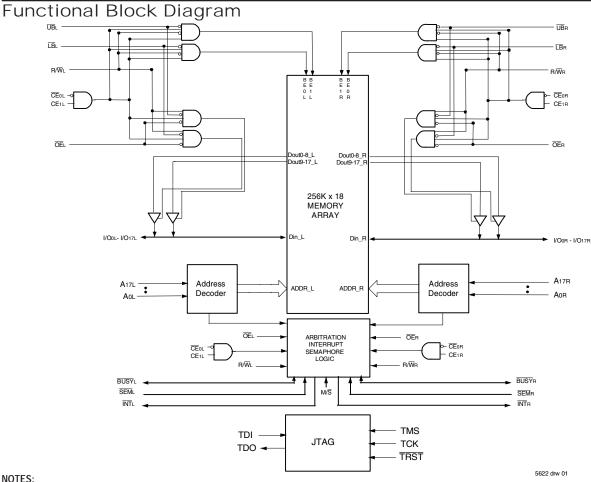
HIGH-SPEED 3.3V 256K x 18 ASYNCHRONOUS DUAL-PORT STATIC RAM

70V631S

Features

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed access
 - Commercial: 10/12/15ns (max.)
 - Industrial: 12ns (max.)
- Dual chip enables allow for depth expansion without external logic
- IDT70V631 easily expands data bus width to 36 bits or more using the Master/Slave select when cascading more than one device
- M/S = ViH for BUSY output flag on Master, $M/\overline{S} = VIL$ for \overline{BUSY} input on Slave
- Busy and Interrupt Flags
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports

- Fully asynchronous operation from either port
- Separate byte controls for multiplexed bus and bus matching compatibility
- Supports JTAG features compliant to IEEE 1149.1
 - Due to limited pin count, JTAG is not supported on the 128-pin TQFP package.
- LVTTL-compatible, single 3.3V (±150mV) power supply for
- LVTTL-compatible, selectable 3.3V (±150mV)/2.5V (±100mV) power supply for I/Os and control signals on each port
- Available in a 128-pin Thin Quad Flatpack, 208-ball fine pitch Ball Grid Array, and 256-ball Ball Grid Array
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information



NOTES:

- BUSY is an input as a Slave (M/S=VIL) and an output when it is a Master (M/S=VIH).
- BUSY and INT are non-tri-state totem-pole outputs (push-pull).

SEPTEMBER 2019

Description

The IDT70V631 is a high-speed 256K x 18 Asynchronous Dual-Port Static RAM. The IDT70V631 is designed to be used as a stand-alone 4608K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 36-bit-or-more word system. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 36-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control,

address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (either $\overline{CE}0$ or CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

The 70V631 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controlled by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

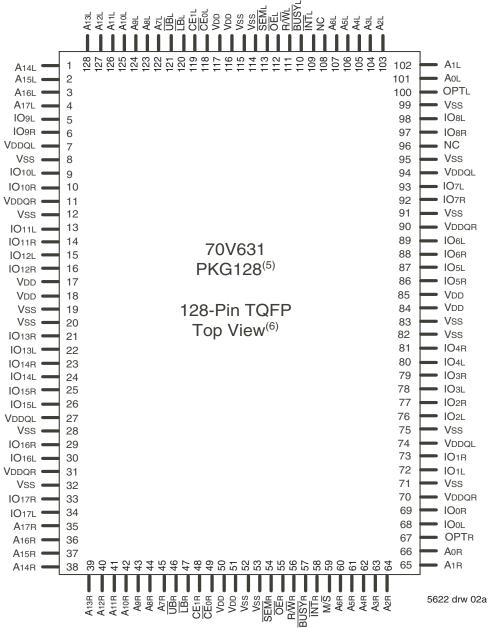
Pin Configurations (1,2,3,4)

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
Α	I/O9L	NC	Vss	TDO	NC	A ₁₆ L	A12L	AsL	NC	VDD	SEML	ĪNTL	A ₄ L	AoL	OPTL	NC	Vss	Α
В	NC	Vss	NC	TDI	A17L	A13L	A9L	NC	CEoL	Vss	BUSYL	A ₅ L	A ₁ L	Vss	VDDQR	I/O ₈ L	NC	В
С	VDDQL	I/O ₉ R	VDDQR	VDD	NC	A14L	A10L	ŪBL	CE ₁ L	Vss	R/WL	A ₆ L	A2L	VDD	I/O8R	NC	Vss	С
D	NC	Vss	I/O _{10L}	NC	A ₁₅ L	A11L	A7L	ŪB∟	VDD	ŌĒL	NC	Азь	V _{DD}	NC	VDDQL	I/O7L	I/O7R	D
Е	I/O11L	NC	VDDQR	I/O10R		-								I/O ₆ L	NC	Vss	NC	Е
F	VDDQL	I/O11R	NC	Vss										Vss	I/O ₆ R	NC	VDDQR	F
G	NC	Vss	I/O12L	NC				7	0) (60	1				NC	VDDQL	I/O ₅ L	NC	G
Н	VDD	NC	VDDQR	I/O12R				В	0V63 F208	(5)				V _{DD}	NC	Vss	I/O ₅ R	Н
J	VDDQL	VDD	Vss	Vss				BF	G20	8(5)				Vss	VDD	Vss	VDDQR	J
K	I/O _{14R}	Vss	I/O13R	Vss					Ball I Vie	_				I/O3R	VDDQL	I/O _{4R}	Vss	K
L	NC	I/O14L	VDDQR	I/O13L										NC	I/O3L	Vss	I/O4L	L
M	VDDQL	NC	I/O _{15R}	Vss										Vss	NC	I/O ₂ R	VDDQR	M
Ν	NC	Vss	NC	I/O _{15L}										I/O1R	VDDQL	NC	I/O2L	Ν
Р	I/O _{16R}	I/O16L	VDDQR	NC	TRST	A ₁₆ R	A 12R	Asr	NC	VDD	SEMR	ĪNTR	A4R	NC	I/O1L	Vss	NC	Р
R	Vss	NC	I/O _{17R}	тск	A 17R	A13R	A ₉ R	NC	CEor	Vss	BUSYR	A ₅ R	A _{1R}	Vss	VDDQL	I/Oor	VDDQR	R
Т	NC	I/O17L	VDDQL	TMS	NC	A _{14R}	A10R	ŪBR	CE _{1R}	Vss	R/WR	A 6R	A ₂ R	Vss	NC	Vss	NC	Т
U	Vss	NC	V _{DD}	NC	A15R	A11R	A7R	LBR	VDD	ŌĒR	M/S	Азп	A ₀ R	VDD	OPTR	NC	I/OoL	U

5622 tbl 02b

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V) and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground.
- 4. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configurations (1,2,3,4,7) (con't.)



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V) and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground.
- 4. Package body is approximately 14mm x 20mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.
- 7. Due to the restricted number of pins, JTAG is not supported in the PK-128 package.



Pin Configuration^(1,2,3,4) (con't.)

70V631 BC256⁽⁵⁾ BCG256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	A 17L	A 14L	A 11L	A 8L	NC	CE1L	OEL	INTL	A 5L	A 2L	A0L	NC	NC
B1	B2	B3	B4	B5	B6	B7	B8	B9	B10	B11	B12	B13	B14	B15	B16
NC	NC	TDO	NC	A 15L	A 12L	A 9L	UBL	CEol	R/WL	NC	A 4L	A 1L	NC	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/ O 9L	Vss	A 16L	A 13L	A 10L	A 7L	NC	LBL	SEML	BUSYL	A 6L	A 3L	OPTL	NC	I/O8L
D1	D2	D3	D4	D5	d6	d7	d8	D9	D10	D11	D12	D13	D14	D15	D16
NC	I/ O 9R	NC	Vdd	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	VDDQR	Vddqr	VDD	NC	NC	I/O8R
E1		E3	E4	E5	E6	E7	E8	E9	E10	E11	E12	E13	E14	E15	E16
I/O10R		NC	VddQL	Vdd	Vdd	V SS	V SS	Vss	V SS	VDD	VDD	Vddqr	NC	I/O7L	I/O7R
F1	F2	F3	F4	F5	F6	F7	F8	F9	F10	F11	F12	F13	F14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	VDD	Vddqr	I/O6R	NC	I/O6L
G1	G2	G3	G4	G5	G6	G7	G8	G9	G10	G11	G12	G13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	V SS	Vss	Vss	Vss	Vss	Vss	VDDQL	I/ O 5L	NC	NC
H1	H2	нз	h4	H5	H6	H7	H8	H9	H10	H11	H12	H13	H14	H15	H16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	V SS	Vss	Vss	Vddql	NC	NC	I/O5R
J1	J2	J3	J4	J5	J6	J7	J8	J9	J10	J11	J12	J13	J14	J15	J16
I/O13L	I/O14R	I/O13R	Vddql	V SS	Vss	V SS	Vss	V SS	V ss	Vss	V SS	Vddqr	I/O4R	I/Озп	I/O4L
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10	K11	K12	K13	K14	K15	К16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	V SS	V SS	Vss	Vss	Vddqr	NC	NC	I/ О 3L
L1	L2	L3	L4	L5	L6	L7	L8	L9	L10	L11	L12	L13	L14	L15	L16
I/O15L	NC	I/O15R	Vddqr	Vdd	Vss	Vss	Vss	Vss	V SS	Vss	VDD	VDDQL	I/O2L	NC	I/O2R
M1	M2	мз	M4	M5	M6	M7	M8	M9	M10	M11	M12	M13	M14	M15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	VDD	Vss	Vss	Vss	V SS	VDD	VDD	VDDQL	I/O1R	I/O1L	NC
N1	N2	N3	N4	N5	n6	N7	n8	n9	N10	N11	N12	N13	N14	N15	N16
NC	I/O17R	NC	Vdd	VDDQR	Vddqr	V DDQL	Vddql	Vddqr	Vddqr	VDDQL	Vddql	VDD	NC	I/O0R	NC
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
NC	I/O17L	TMS	A 16R	A 13R	A 10R	A 7R	NC	LBR	SEMR	BUSYR	A 6R	A 3R	NC	NC	I/OoL
R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	R13	R14	R15	R16
NC	NC	TRST	NC	A 15R	A 12R	A 9R	UBr	CEor	R/WR	M/S	A 4R	A 1R	OPTR	NC	NC
T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11	T12	T13	T14	T15	T16
NC	TCK	NC	A 17R	A 14R	A 11R	A 8R	NC	CE1R	OEr	INTR	A 5R	A 2R	A 0R	NC	NC

5622 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.



Pin Names

Left Port	Right Port	Names		
Œ0L, CE1L	Œ0R, CE1R	Chip Enables		
R/WL	R/W̄R	Read/Write Enable		
ŌĒL	OE R	Output Enable		
AOL - A17L	A0R - A17R	Address		
I/O0L - I/O17L	I/Oor - I/O17R	Data Input/Output		
SEML	<u>SEM</u> R	Semaphore Enable		
ĪNTL	ĪNTR	Interrupt Flag		
BUSYL	BUS Y _R	Busy Flag		
Ū <u>B</u> L	ŪB̄R	Upper Byte Select		
<u>LB</u> ∟	<u>∏</u> R	Lower Byte Select		
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾		
OPTL	OPTr	Option for selecting VDDax ^(1,2)		
M	√S	Master or Slave Select		
V	DD	Power (3.3V) ⁽¹⁾		
V	SS	Ground (0V)		
Т	DI	Test Data Input		
TI	00	Test Data Output		
TO	CK	Test Logic Clock (10MHz)		
TN	MS	Test Mode Select		
ĀĪ	RST	Reset (Initialize TAP Controller)		

5622 tbl 01

- VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on I/Ox.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDOX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDOX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.



Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control⁽¹⁾

ŌĒ	SEM	ΣĒ₀	CE1	ŪB	ĪΒ	R/W	Byte 1 I/O ₉₋₁₇	Byte 0 I/O ₀₋₈	MODE
Х	Н	Н	Χ	Χ	Х	Χ	High-Z	High-Z	Deselected-Power Down
Х	Н	Χ	L	Χ	Х	Χ	High-Z	High-Z	Deselected-Power Down
Х	Н	L	Н	Н	Н	Χ	High-Z	High-Z	Both Bytes Deselected
Х	Н	L	Н	Н	L	L	High-Z	DIN	Write to Byte 0 Only
Х	Н	L	Н	L	Н	L	Din	High-Z	Write to Byte 1 Only
Х	Н	L	Н	L	L	L	Din	DIN	Write to Both Bytes
L	Н	L	Н	Н	L	Н	High-Z	Douт	Read Byte 0 Only
L	Н	L	Н	L	Н	Н	Dоит	High-Z	Read Byte 1 Only
L	Н	L	Н	L	L	Н	Dоит	Douт	Read Both Bytes
Н	Н	L	Н	L	L	Χ	High-Z	High-Z	Outputs Disabled

NOTE:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

<u>Truth Table II - Semaphore Read/Write Control⁽¹⁾</u>

	Inputs ⁽¹⁾					Outputs		
ΖĒ	R/W	ŌĒ	ŪB	LB	SEM	I/O1-17	I/Oo	Mode
Н	Н	L	L	L	L	DATAout	DATAout	Read Data in Semaphore Flag ⁽³⁾
Н	1	Χ	Χ	L	L	Х	DATAIN	Write I/Oo into Semaphore Flag
L	Χ	Χ	Χ	Χ	L			Not Allowed

NOTE:

5622 tbl 03

- 1. There are eight semaphore flags written to I/Oo and read from all the I/Os (I/Oo-I/O17). These eight semaphore flags are addressed by Ao-A2.
- 2. $\overline{CE} = L$ occurs when $\overline{\overline{CE}}_0 = V_{IL}$ and $CE_1 = V_{IH}$.
- 3. Each byte is controlled by the respective \overline{UB} and \overline{LB} . To read data \overline{UB} and/or \overline{LB} = V_{IL}.



Industrial and Commercial Temperature Ranges

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	V _{DD}
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTE:

5622 tbl 04

1. This is the parameter Ta. This is the "instant on" case temperature.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	50	mA

NOTES:

5622 tbl 05

5622 tbl 08

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may
 cause permanent damage to the device. This is a stress rating only and functional
 operation of the device at these or any other conditions above those indicated
 in the operational sections of this specification is not implied. Exposure to absolute
 maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.

Capacitance⁽¹⁾

$(TA = +25^{\circ}C, F = 1.0MHz) TQFP ONLY$

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF

NOTES:

- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references CI/o.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit			
VDD	Core Supply Voltage	3.15	3.3	3.45	٧			
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	٧			
Vss	Ground	0	0	0	٧			
Vн	Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7	-	VDDQ + 100mV ⁽²⁾	V			
Vн	Input High Voltage - I/O ⁽³⁾	1.7		VDDQ + 100mV ⁽²⁾	٧			
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.7	٧			
	5622 tbl 06							

NOTES:

- 1. V_{IL ≥} -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 100mV.
- 3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDDX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	٧
Vss	Ground	0	0	0	V
VIH	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0	_	VDDQ + 150mV ⁽²⁾	V
V⊪	Input High Voltage - I/O ⁽³⁾	2.0		VDDQ + 150mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

5622 tbl 07

- 1. $V_{IL \ge}$ -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 150mV.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDOX for that port must be supplied as indicated above.



Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating

Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

				631S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ	_	10	μΑ
ILO	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{DDQ}$		10	μΑ
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, VDDQ = Min.		0.4	V
Voh (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.	_	0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTE:

5622 tbl 09

- 1. At V_{DD} ≤ 2.0V input leakages are undefined.
- 2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}$ (VDD = 3.3V \pm 150mV)

70V631S10 70V631S12 70V631S15 Com'l Only Com'l Com'l & Ind Typ.(4) Typ. (4) Typ. (4) Symbol Parameter **Test Condition** Version Max. Мах. Max. Unit Dynamic Operating CEL and CER= VIL, mA COM'L 340 S 500 315 465 300 440 Current (Both Outputs Disabled, IND S Ports Active) $f = fMAX^{(1)}$ 365 515 ISB1 Standby Current $\overline{CE}L = \overline{CE}R = VIH$ COM'L mA S 115 165 75 100 (Both Ports - TTL $f = fMAX^{(1)}$ IND S 150 115 Level Inputs) Standby Current \overline{CE} "A" = VIL and \overline{CE} "B" = VIH⁽⁵⁾ ISB2 COM'L S 225 340 200 325 175 mΑ (One Port - TTL Active Port Outputs Disabled, IND S 225 365 Level Inputs) f=fMAX⁽¹⁾ Full Standby Current Both Ports CEL and ISB3 mA S COM'L 3 3 15 15 3 15 (Both Ports - CMOS CER > VDDQ - 0.2V, Level Inputs) $VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$, IND S 6 15 Full Standby Current ISB4 mA \overline{CE} "A" $\leq 0.2V$ and S COM'L 195 170 220 335 320 310 (One Port - CMOS \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$ Level Inputs) $VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$, Active Port, Outputs Disabled, IND S 220 360 $f = fMAX^{(1)}$

NOTES: 5622 tbl 10

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, $TA = 25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0X} = V_{IL} \text{ and } CE_{1X} = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{V}\text{DDQ}$ 0.2 V
 - $\overline{\text{CE}}$ x \geq VDDQ 0.2V means $\overline{\text{CE}}$ 0x \geq VDDQ 0.2V or CE1x 0.2V
 - "X" represents "L" for left port or "R" for right port.



AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels	GND to 3.0V / GND to 2.5V
Input Rise/Fall Times	2ns Max.
Input Timing Reference Levels	1.5V/1.25V
Output Reference Levels	1.5V/1.25V
Output Load	Figures 1 and 2

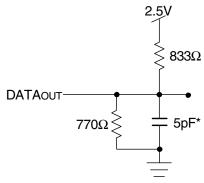


Figure 2. Output Test Load

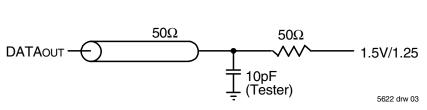


Figure 1. AC Output Test load.

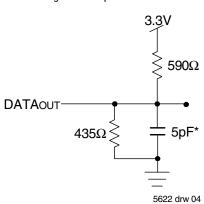


Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

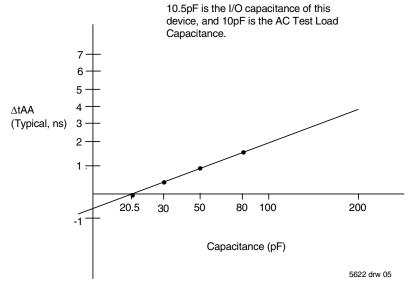


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾

		70V631S10 Com'l Only		70V631S12 Com'l & Ind		70V631S15 Com'l		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	10	_	12	_	15		ns
taa	Address Access Time		10	_	12	_	15	ns
tace	Chip Enable Access Time ⁽³⁾	_	10	_	12	_	15	ns
tabe	Byte Enable Access Time ⁽³⁾	_	5	_	6	_	7	ns
taoe	Output Enable Access Time	_	5	_	6	_	7	ns
tон	Output Hold from Address Change	3	_	3	_	3		ns
tLZ	Output Low-Z Time ^(1,2)	0		0		0		ns
tHZ	Output High-Z Time ^(1,2)	0	4	0	6	0	8	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0	_	0	-	0		ns
tpD	Chip Disable to Power Down Time ⁽²⁾	_	10	_	10	_	15	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)		4	_	6	_	8	ns
tsaa	Semaphore Address Access Time	3	10	3	12	3	20	ns

5622 tbl 12

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

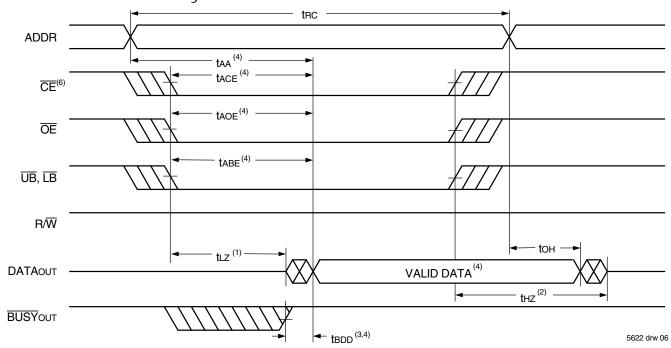
		70V631S10 Com'l Only		70V631S12 Com'l & Ind		70V631S15 Com'l		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time	10	_	12	_	15	_	ns
tew	Chip Enable to End-of-Write ⁽³⁾	8	_	10	_	12	_	ns
taw	Address Valid to End-of-Write	8	_	10	_	12		ns
tas	Address Set-up Time ⁽³⁾	0	_	0	_	0		ns
twp	Write Pulse Width	8	_	10	_	12		ns
twr	Write Recovery Time	0	_	0	_	0		ns
tow	Data Valid to End-of-Write	6	_	8	_	10	_	ns
tон	Data Hold Time ⁽⁴⁾	0	_	0	_	0		ns
twz	Write Enable to Output in High-Z ^(1,2)	_	4	_	4	_	4	ns
tow	Output Active from End-of-Write ^(1,2,4)	0	_	0	_	0		ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	5	_	ns
tsps	SEM Flag Contention Window	5	_	5		5		ns

NOTES:

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access RAM, \overrightarrow{CE} = V_IL and \overrightarrow{SEM} = V_IH. To access semaphore, \overrightarrow{CE} = V_IH and \overline{SEM} = V_IL. Either condition must be valid for the entire tew time.
- 4. The specification for ton must be met by the device supplying write data to the RAM under all operating conditions. Although ton and tow values will vary over voltage and temperature, the actual ton will always be smaller than the actual tow.
- 5. These values are valid regardless of the power supply level selected for I/O and control signals (3.3V/2.5V). See page 5 for details.



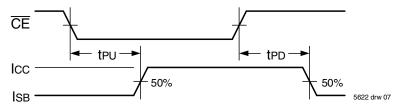
Waveform of Read Cycles⁽⁵⁾



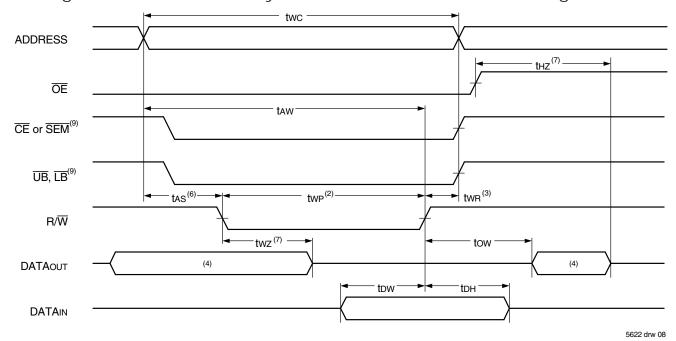
NOTES:

- 1. Timing depends on which signal is asserted last, \overline{OE} , \overline{CE} , \overline{LB} or \overline{UB} .
- 2. Timing depends on which signal is de-asserted first \overline{CE} , \overline{OE} , \overline{LB} or \overline{UB} .
- 3. tepp delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last taoe, tace, taa or tBDD.
- 5. $\overline{SEM} = VIH$.

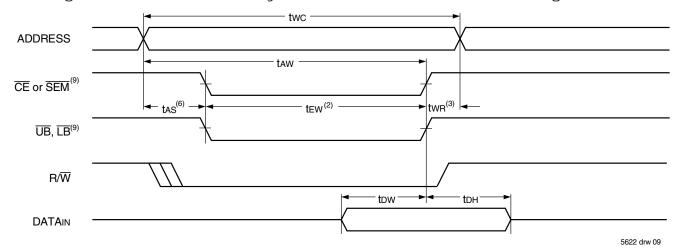
Timing of Power-Up Power-Down



Timing Waveform of Write Cycle No. 1, R/W Controlled Timing (1,5,8)

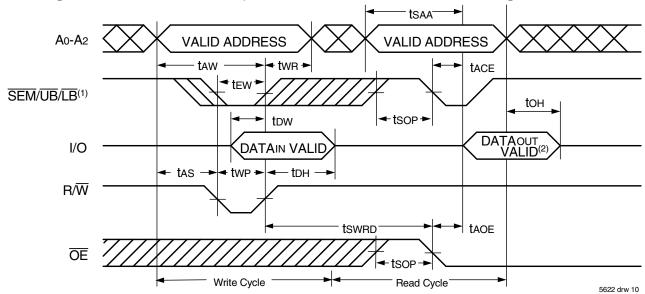


Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



- 1. R/\overline{W} or \overline{CE} or $\overline{BE}n = VIH$ during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a $\overline{CE} = VIL$ and a $R\overline{W} = VIL$ for memory array writing cycle.
- 3. two is measured from the earlier of $\overline{\text{CE}}$ or $\overline{\text{R/W}}$ (or $\overline{\text{SEM}}$ or $\overline{\text{R/W}}$) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the $\overline{\text{CE}}$ or $\overline{\text{SEM}} = \text{VIL}$ transition occurs simultaneously with or after the $\overline{\text{R/W}} = \text{VIL}$ transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, $\overline{\text{CE}}$ or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If $\overline{OE} = V_{IL}$ during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If $\overline{OE} = V_{IH}$ during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, $\overline{\text{CE}} = \text{VIL}$ and $\overline{\text{SEM}} = \text{VIH}$. To access semaphore, $\overline{\text{CE}} = \text{VIH}$ and $\overline{\text{SEM}} = \text{VIL}$. tew must be met for either condition.

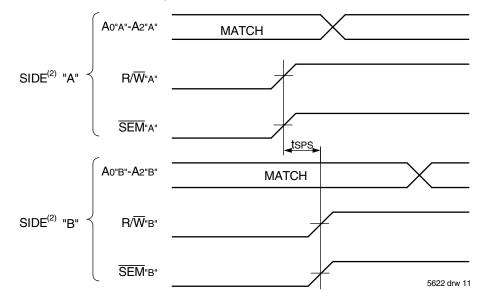
Timing Waveform of Semaphore Read after Write Timing, Either Side(1)



NOTES:

- 1. $\overline{CE} = VIH \text{ or } \overline{UB} \text{ and } \overline{LB} = VIH \text{ for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table). Refer also to Truth Table II for appropriate <math>\overline{UB}/\overline{LB}$ controls.
- 2. "DATAOUT VALID" represents all I/O's (I/Oo I/O17) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



- 1. Dor = Dol = VIL, $\overline{CE}L = \overline{CE}R = VIH$. Refer also to Truth Table II for appropriate $\overline{UB/LB}$ controls.
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
- 3. This parameter is measured from R/W*a" or SEM*a* going HIGH to R/W*B* or SEM*B* going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will be granted the semaphore flag.



Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

Comphal	Parameter	70V631S10 Com'l Only		Co	31S12 m'l Ind	Co		Unit
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Uniii
BUSY TIMING	(M/S=VIH)							
t BAA	BUSY Access Time from Address Match		10	1	12	_	15	ns
t BDA	BUSY Disable Time from Address Not Matched		10	_	12	_	15	ns
t BAC	BUSY Access Time from Chip Enable Low		10	_	12	_	15	ns
tBDC	BUSY Disable Time from Chip Enable High		10	_	12	_	15	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5	_	5	_	ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		10	_	12	_	15	ns
twн	Write Hold After BUSY ⁽⁵⁾	8	_	10		12		ns
BUSY TIMING	(M/S=VIL)							
twB	BUSY Input to Write ⁽⁴⁾	0		0		0	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	8	_	10	_	12		ns
PORT-TO-POR	T DELAY TIMING							
twdd	Write Pulse to Data Delay ⁽¹⁾		22		25		30	ns
tDDD	Write Data Valid to Read Data Delay ⁽¹⁾		20	_	22		25	ns

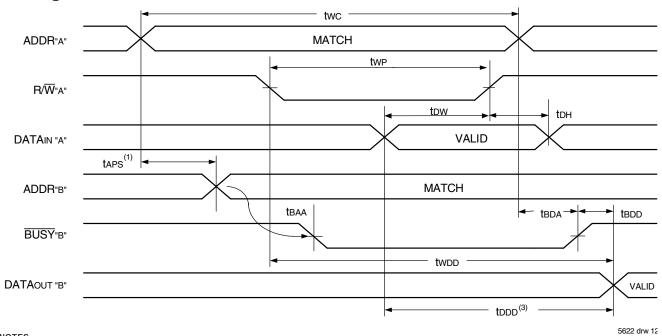
5622 tbl 14

- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = Vi+)".
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of the Max. spec, twdd twp (actual), or tddd tdw (actual).
- 4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".



Industrial and Commercial Temperature Ranges

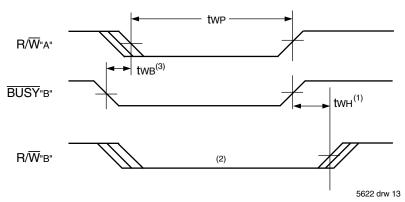
Timing Waveform of Write with Port-to-Port Read and $\overline{\textbf{BUSY}}$ (M/ $\overline{\textbf{S}}$ = VIH) $^{(2,4,5)}$



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = V_{IL}$ (SLAVE).
- 2. $\overline{CE}_L = \overline{CE}_R = V_{IL}$.
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If $M/\overline{S} = VIL$ (slave), \overline{BUSY} is an input. Then for this example $\overline{BUSY}^*A^* = VIH$ and \overline{BUSY}^*B^* input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with $\overline{\mathbf{BUSY}}$ (M/ $\overline{\mathbf{S}}$ = VIL)

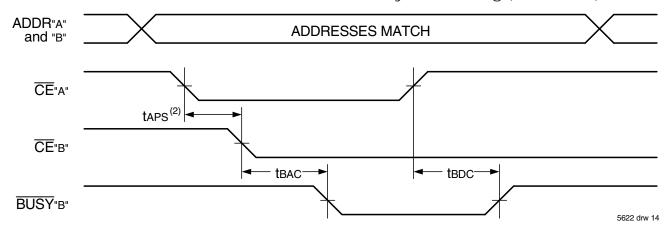


- 1. twn must be met for both $\overline{\text{BUSY}}$ input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY "B" goes HIGH.
- 3. twb is only for the 'slave' version.

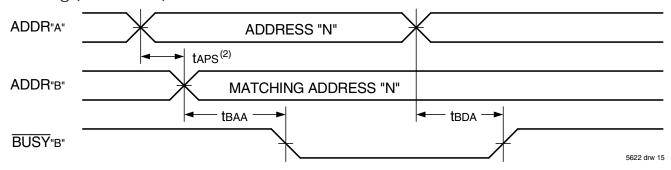


Industrial and Commercial Temperature Ranges

Waveform of **BUSY** Arbitration Controlled by **CE** Timing (M/**S** = V_IH)⁽¹⁾



Waveform of $\overline{\textbf{BUSY}}$ Arbitration Cycle Controlled by Address Match Timing (M/ $\overline{\textbf{S}}$ = VIH)⁽¹⁾



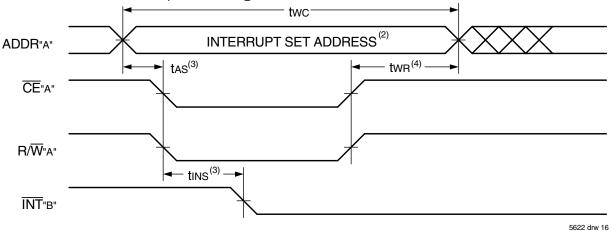
NOTES

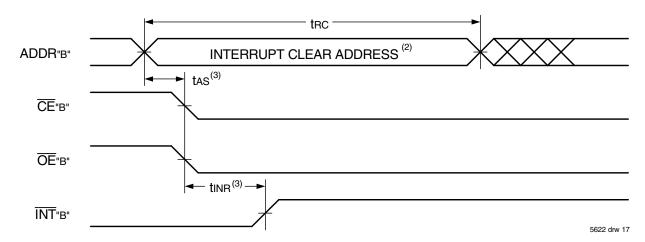
- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

		70V631S10 Com'l Only		70V631S12 Com'l & Ind		70V631S15 Com'l		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUPT TIMING								
tas	Address Set-up Time	0	_	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tins	Interrupt Set Time	_	10	_	12	_	15	ns
tinr	Interrupt Reset Time	_	10		12	_	15	ns

Waveform of Interrupt Timing⁽¹⁾





NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. Refer to Interrupt Truth Table.
- Timing depends on which enable signal (CE or R/W) is asserted last.
 Timing depends on which enable signal (CE or R/W) is de-asserted first.

Truth Table III — Interrupt Flag^(1,4)

	Left Port Right Port									
R/ W ∟	<u>C</u> Ē∟	ŌĒL	A17L-A0L	ĪNTL	R/W̄R	C ER	OE R	A17R-A0R	Ī NT R	Function
L	L	Х	3FFFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	3FFFE	Х	Set Left INTL Flag
Х	L	L	3FFFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$.
- 2. If $\overline{BUSY}L = VIL$, then no change.
- 3. If $\overline{BUSY}_R = V_{IL}$, then no change.
- 4. INTL and INTR must be initialized at power-up.

Truth Table IV —

Address **BUSY** Arbitration

Inputs			Out	puts	
<u>C</u> E∟	CE _R	Aol-A17L Aor-A17R	BUS YL(1)	BUSY _R (1)	Function
Х	Χ	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

5622 tbl 17

NOTES:

- 1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V631 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.
- 2. "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Truth Table V — Example of Semaphore Procurement Sequence (1,2,3)

Functions	Do - D17 Left	Do - D17 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES: 5622 tol 18

- 1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V631.
- 2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O17). These eight semaphores are addressed by Ao A2.
- 3. $\overline{CE} = VIH$, $\overline{SEM} = VIL$ to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT70V631 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V631 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ 0 and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ = HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag $(\overline{INT}L)$ is asserted when the right port writes to memory location

3FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{W}R = VIL$ per the Truth Table. The left port clears the interrupt through access of address location 3FFFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 3FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 3FFFF. The message (18 bits) at 3FFFE or 3FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FFFE and 3FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of \overline{BUSY} logic is not desirable, the \overline{BUSY} logic can be disabled by placing the part in slave mode with the $\overline{M/S}$ pin. Once in slave mode the \overline{BUSY} pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the \overline{BUSY} pins HIGH. If desired, unintended write operations can be prevented to a port by tying the \overline{BUSY} pin for that port LOW.

The BUSY outputs on the IDT70V631 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

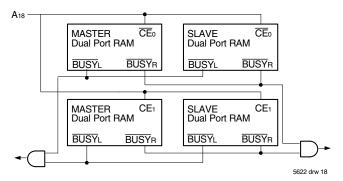


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V631 RAMs.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V631 RAM array in width while using $\overline{\text{BUSY}}$ logic, one master part is used to decide which side of the RAMs array will receive a $\overline{\text{BUSY}}$ indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the $\overline{\text{BUSY}}$ signal as a write inhibit signal. Thus on the IDT70V631 RAM the $\overline{\text{BUSY}}$ pin is an output if the part is used as a master (M/\$\overline{\Sigma}\$ pin = VIL), and the \$\overline{\text{BUSY}}\$ pin is an input if the part used as a slave (M/\$\overline{\Sigma}\$ pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating $\overline{\text{BUSY}}$ on one side of the array and another master indicating $\overline{\text{BUSY}}$ on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration on a master is based on the chip enable and

address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a $\overline{\text{BUSY}}$ flag to be output from the master before the actual write pulse can be initiated with the R/\overline{W} signal. Failure to

observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V631 is an extremely fast Dual-Port 256K x 18 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, with both ports being completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from or written to at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by $\overline{\text{CE}}$, the Dual-Port RAM enable, and $\overline{\text{SEM}}$, the semaphore enable. The $\overline{\text{CE}}$ and $\overline{\text{SEM}}$ pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected.

Systems which can best use the IDT70V631 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V631s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V631 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then

verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70V631 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the $\overline{\text{SEM}}$ pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, $\overline{\text{CE}}$, $\overline{\text{R/W}}$ and $\overline{\text{LB/UB}}$) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins Ao – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore, byte select (\overline{SEM} , $\overline{LB}/\overline{UB}$) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (\overline{SEM} or \overline{OE}) to go inactive or the output will never change. However, during reads \overline{LB} and \overline{UB} function only as an output for semaphore. They do not have any influence on the semaphore control logic.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in

question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during

the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will

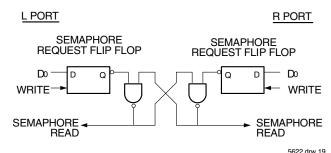


Figure 4. IDT70V631 Semaphore Logic

continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

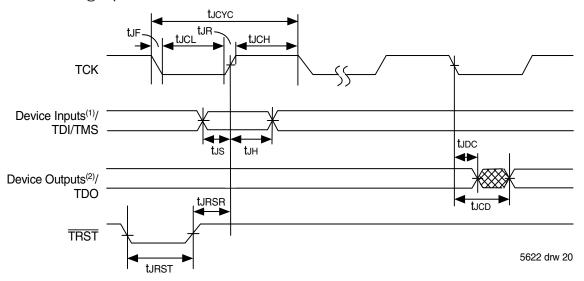
The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.



JTAG Timing Specifications



NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

JTAG AC Electrical Characteristics^(1,2,3,4)

Symbol	Parameter	Min.	Max.	Units
tucyc	JTAG Clock Input Period	100	-	ns
tлсн	JTAG Clock HIGH	40	_	ns
tucL	JTAG Clock Low	40	_	ns
tır	JTAG Clock Rise Time	_	3 ⁽¹⁾	ns
₩	JTAG Clock Fall Time	_	3 ⁽¹⁾	ns
turst	JTAG Reset	50	_	ns
tursr	JTAG Reset Recovery	50	_	ns
tico	JTAG Data Output	—	25	ns
tudo	JTAG Data Output Hold	0	_	ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15	_	ns

NOTES:

- 1. Guaranteed by design.
- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- 4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.



Industrial and Commercial Temperature Ranges

Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x304	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

5622 tbl 20

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5622 tbl 21

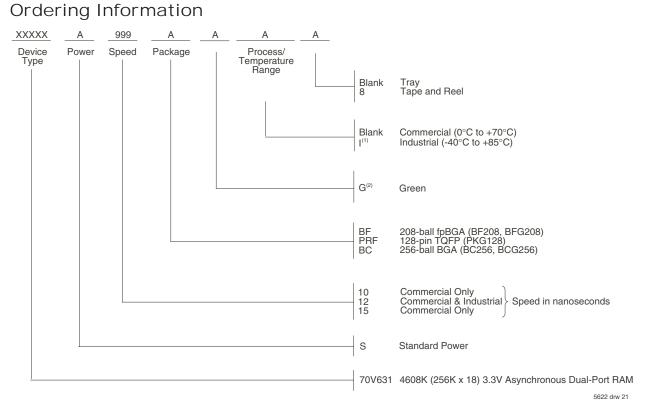
System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES

- 1. Device outputs = All device outputs except TDO.
- 2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.
- 3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.





NOTES:

- $1. \quad \text{Contact your local sales of fice for industrial temp range for other speeds, packages and powers.} \\$
- Green parts available for specific speeds, packages and powers contact your local sales office.
 LEAD FINISH (SnPb) parts are Obsolete excluding BGA & fpBGA. Product Discontinuation Notice PDN# SP-17-02
 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
10	70V631S10BC	BC256	CABGA	С
	70V631S10BC8	BC256	CABGA	С
	70V631S10BCG	BCG256	CABGA	С
	70V631S10BCG8	BCG256	CABGA	С
	70V631S10BF	BF208	CABGA	С
	70V631S10BF8	BF208	CABGA	С
	70V631S10BFG	BFG208	CABGA	С
	70V631S10BFG8	BFG208	CABGA	С
	70V631S10PRFG	PKG128	TQFP	С
12	70V631S12BC	BC256	CABGA	С
	70V631S12BC8	BC256	CABGA	С
	70V631S12BCI	BC256	CABGA	- 1
	70V631S12BCl8	BC256	CABGA	- 1
	70V631S12BF	BF208	CABGA	С
	70V631S12BF8	BF208	CABGA	С
	70V631S12BFGI	BFG208	CABGA	1
	70V631S12BFGl8	BFG208	CABGA	- 1
	70V631S12BFI	BF208	CABGA	I
	70V631S12BFl8	BF208	CABGA	- 1
	70V631S12PRFGI	PKG128	TQFP	- 1

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
15	70V631S15BC	BC256	CABGA	С
	70V631S15BC8	BC256	CABGA	С
	70V631S15BF	BF208	CABGA	С
	70V631S15BF8	BF208	CABGA	С



Industrial and Commercial Temperature Ranges

Datasheet Document History

06/01/00: Initial Public Offering

08/07/00: Page 6, 13 & 20 Inserted additional \overline{LB} and \overline{UB} information 06/20/01: Page 1 Added JTAG information for TQFP package

Page 14 Increased BUSY TIMING parameters tBDA, tBAC, tBDC and tBDD for all speeds

Page 21 Changed maximum value for JTAG AC Electrical Characteristics for tuco from 20ns to 25ns

08/08/01: Page 3 Corrected pin 4 designation error from A17R to A17L on PK-128 pinout

10/01/03: Removed Preliminary status

Page 2, 3 & 4 Added date revision for pin configurations

Page 8, 10, 14 & 16 Removed I-temp 15ns speed from DC & AC Electrical Characteristics Tables

Page 23 Removed I-temp 15ns speed from ordering information

Added I-temp footnote to ordering information Page 1 & 23 Replaced ™ logo with ® logo Page 8 Corrected a typo in the DC Chars table

07/25/08: Page 8 Corrected a typo in the DC Chars table 01/29/09: Page 23 Removed "IDT" from orderable part number

10/23/13: Page 1 Added green availability to Features

Page 23 Added green and T&R indicators to ordering information

12/15/17: Product Discontinuation Notice - PDN# SP-17-02

Last time buy expires June 15, 2018

09/18/19: Page 2, 3 & 4 Updated package codes

Page 23 Added Orderable Part Information table

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